

SQD50N06-09L Automotive N-Channel

60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.009				
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.013				
I _D (A)	50				
Configuration	Single				



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET
- \bullet 100 % R_{g} and UIS Tested
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified^d



ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD50N06-09L-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unles		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	60	.,
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C ^a	1	50	
	T _C = 125 °C	I _D	49	
Continuous Source Current (Diode Conduction) ^a		Is	50	А
Pulsed Drain Current ^b		I _{DM}	200	
Single Pulse Avalanche Energy	L = 0.1 mH	I _{AS}	48	
Single Pulse Avalanche Current	L = 0.1 MH	E _{AS}	115	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	В	136	W
	T _C = 125 °C	P_{D}	45	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R_{thJC}	1.1	C/VV	

Notes

a. Package limited.

Top View

- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		60	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu A$		2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 60 V	=	-	1.0		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	=	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	=.	-	250	1	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	=	0.0071	0.0090	Ω	
Drain Cauras On State Besistance	В	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.016		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.019		
		V _{GS} = 4.5 V	I _D = 10 A	-	0.0094	0.013		
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		=.	62	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			=	2451	3065	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	=	435	545		
Reverse Transfer Capacitance	C _{rss}			=.	192	240		
Total Gate Charge ^c	Qg			=	48	72		
Gate-Source Charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 50 \text{ A}$	=	7.1	-	nC	
Gate-Drain Charge ^c	Q_{gd}		<u> </u>	=	13.5	-		
Gate Resistance	Rg	f = 1 MHz		0.85	1.7	2.6	Ω	
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 30 \text{ V, } R_L = 0.6 \Omega$ $I_D \cong 50 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$		=.	10	15		
Rise Time ^c	t _r			=.	11	17	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	27	41		
Fall Time ^c	t _f			-	8	12		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			=	-	200	Α	
Forward Voltage	V_{SD}	I _F = 20 A, V _{GS} = 0 V		-	0.82	1.5	V	

Notes

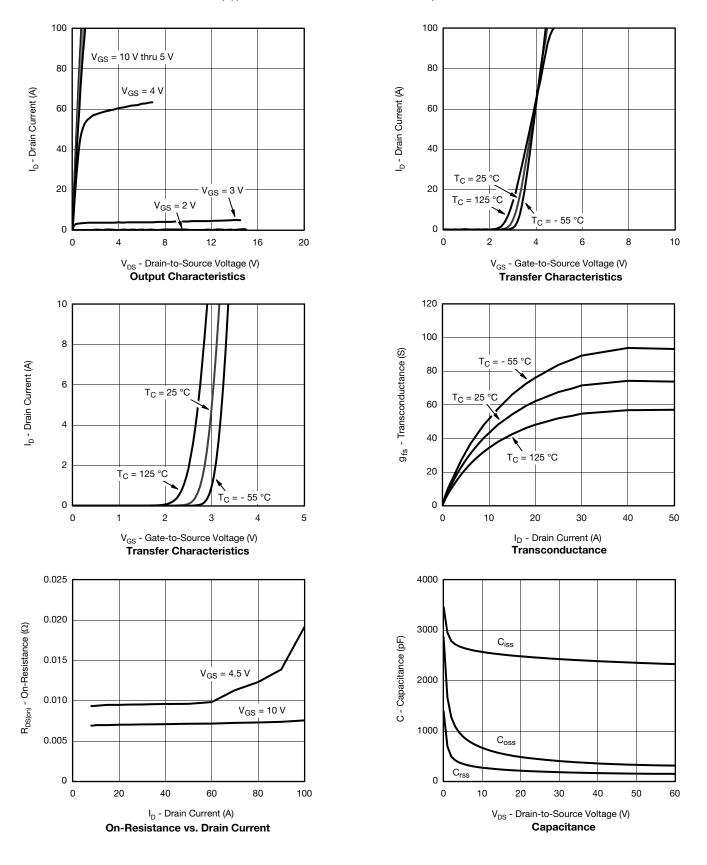
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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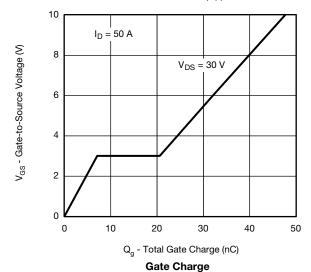
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

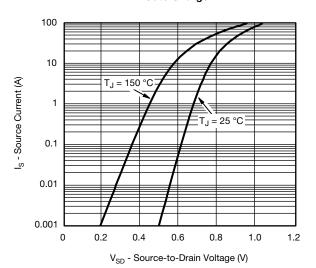


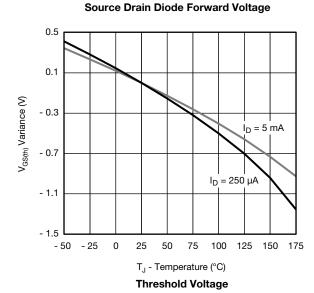


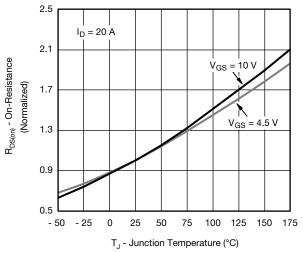
Automotive P-Channel 60 V (D-S) 175 °C MOSFET

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

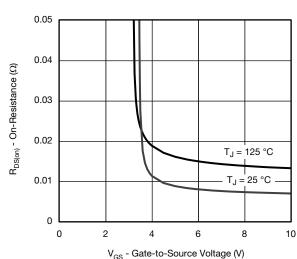




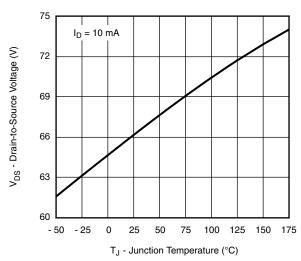








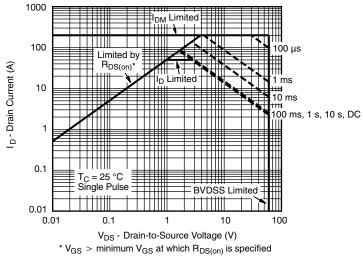
On-Resistance vs. Gate-to-Source Voltage



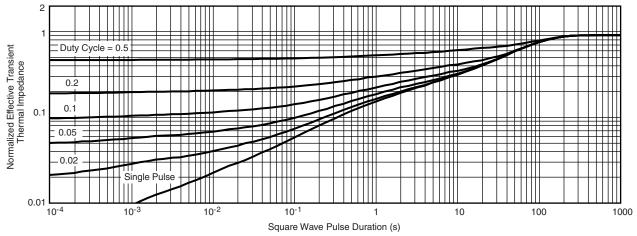
Drain Source Breakdown vs. Junction Temperature

Automotive P-Channel 60 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



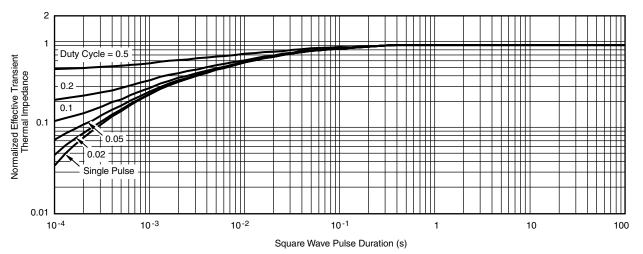
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

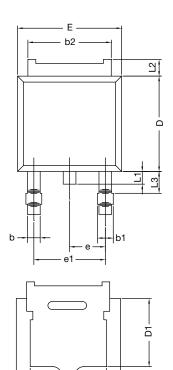
Note

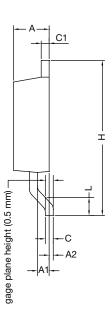
- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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TO-252AA CASE OUTLINE





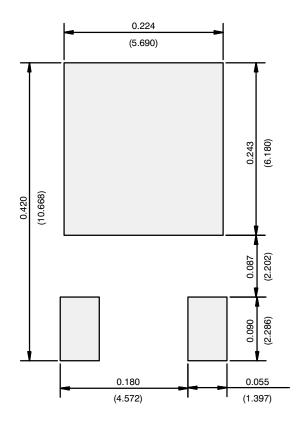
	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57	BSC	0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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SQD50P03-07 Automotive P-Channel 60 V (D-S) 175 °C MOSFET

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